

## **INCHANGE SEMICONDUCTOR**

## isc Silicon PNP Power Transistor

# 2SB1315

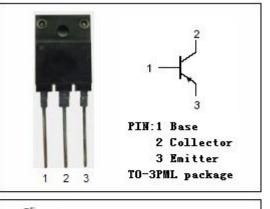
### DESCRIPTION

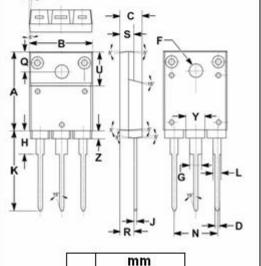
- · Collector-Emitter Breakdown Voltage-
- : V<sub>(BR)CEO</sub>= -120V(Min)
- Good Linearity of h<sub>FE</sub>
- Complement to Type 2SD1977
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

- · Audio frequency power amplifier applications
- · Recommend for 45-55W audio frequency amplifier output stage applications

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)				
SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-120	v	
V <sub>CEO</sub>	Collector-Emitter Voltage	-120	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V	
lc	Collector Current-Continuous	-8	A	
Ісм	Collector Current-Peak	-12	A	
Pc	Collector Power Dissipation @ $T_a=25^{\circ}C$	3.5	W	
	Collector Power Dissipation @ $T_c=25^{\circ}C$	65		
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	





DIM	MIN	MAX
Α	19.90	20.10
В	15.75	16.10
С	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.20
Н	5.90	6.10
J	0.595	0.70
Κ	21.10	22.50
L	1.90	2.25
Ν	10.80	11.00
0	4.90	5.10
R	3.75	3.95
S	3.20	3.60
U	9.90	10.10
Y	4.20	4.90
Ζ	1.90	2.10

isc website: www.iscsemi.com



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## **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25^{\circ}\!\!\!^{\circ}\!\!^{\circ}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -5.0A; I <sub>B</sub> = -0.5A			-1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -5.0A; I <sub>B</sub> = -0.5A			-2.0	V
I <sub>сво</sub>	Collector Cutoff Current	V <sub>CB</sub> = -120V ; I <sub>E</sub> =0			-50	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> =0			-50	μ <b>Α</b>
h <sub>FE-1</sub>	DC Current Gain	Ic= -50mA; Vce= -5V	45			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V	60		320	
Сов	Output Capacitance	I <sub>E</sub> =0; V <sub>CB</sub> = -10V; f <sub>test</sub> = 1.0MHz		200		pF

#### h<sub>FE-2</sub> Classifications

Μ	L	к		
60-120	100-200	160-320		

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